



10191/1614

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Inventor : Richard SPITZ et al.  
Serial No. : 09/720,720  
Filed : February 28, 2001  
For : METHOD FOR ELIMINATING DEFECTS IN SILICON  
ELEMENTS THROUGH SELECTIVE ETCHING  
Examiner : TRAN, Binh  
Art Unit : 1765  
Confirmation No. : 3872

Commissioner for Patents  
Washington, D.C. 20231

I hereby certify that this correspondence is being deposited with the  
United States Postal Service as first class mail in an envelope addressed  
to: Commissioner for Patents, Washington, D.C. 20231 on

Date: January 28, 2003

Reg. No. 36,197

Signature:

Jong H. Lee

**AMENDMENT**

SIR:

This Amendment addresses the Office Action mailed October 1, 2002, and it is respectfully requested that the above-identified application be amended as follows.

**In the Claims:**

Please cancel Claim 26. Please amend Claims 16, 17, 20, 21 and 29 as shown below:

16. (Amended) A method for substantially eliminating at least one of eruptions, impurities and damage in a crystal lattice, the method comprising the steps of:

providing a surface-plated, sawn-out part of a silicon wafer;

selectively drying the at least one silicon element by heating the at least one silicon element with a radiation heater in a vacuum at a pressure of less than about 0.1  
atm; and